

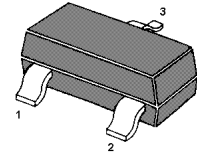
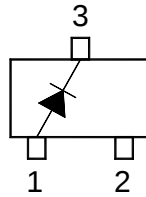
SB411D

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply

Features

- Small surface mounting type.
- High reliability.



TO-236 Plastic Package

Marking

Marking Code: **FE**

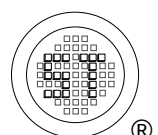
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Reverse Voltage	V_R	20	V
Mean Rectifying Current	I_o	0.5	A
Peak Forward Surge Current ¹⁾	I_{FSM}	3	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +125	$^\circ\text{C}$

¹⁾ 60Hz for 1 $\varnothing$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Typ	Max	Unit
Forward Voltage at $I_F = 10\text{mA}$ at $I_F = 500\text{mA}$	V_F	- -	- -	0.3 0.5	V
Reverse Current at $V_R = 10\text{V}$	I_R	-	-	30	μA
Capacitance Between Terminals at $V_R = 10\text{V}$, $f = 1\text{MHz}$	C_T	-	20	-	pF



Dated : 21/10/2005

●Electrical characteristic curves (Ta = 25°C)

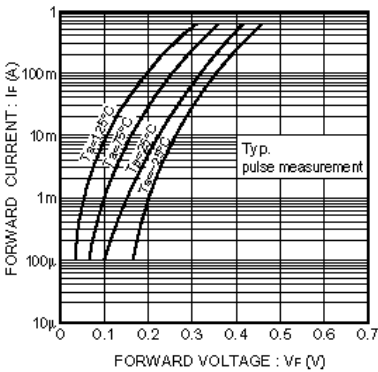


Fig. 1 Forward characteristics

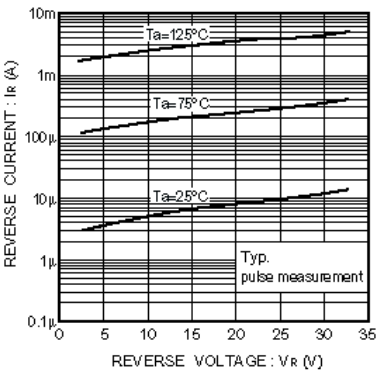


Fig. 2 Reverse characteristics

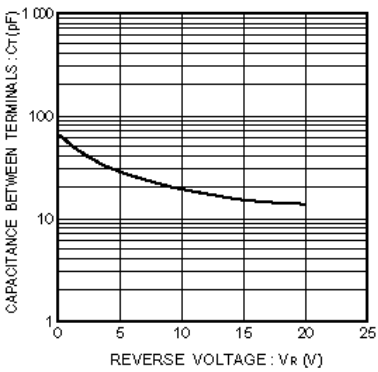


Fig. 3 Capacitance between terminals characteristic

